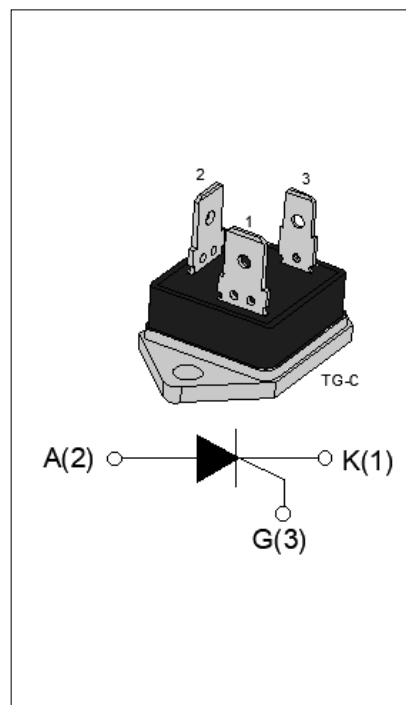




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT855T SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Complying with UL standards (File ref: E252906). Package TG-C is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	55	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	10-50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 71^{\circ}C$)	$I_{T(AV)}$	35	A
RMS on-state current ($T_c \leq 71^{\circ}C$)	$I_{T(RMS)}$	55	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	700	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		750	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	2450	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$)	di/dt	200	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^{\circ}C$)	I_{GM}	10	A

Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	10	-	50	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C } R_L=3.3\text{K}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=500\text{mA}$	-	-	100	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$	1500	-	-	V/ μs
t_{on}	$I_G=50\text{mA } I_A=500\text{mA } I_R=50\text{mA}$ $T_j=25^\circ\text{C}$	-	4	-	μs
t_{off}		-	130	-	

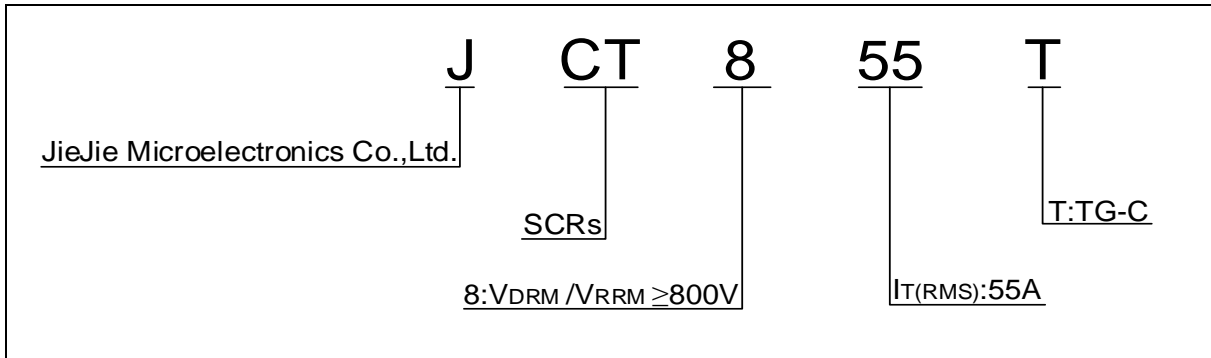
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=80\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.76	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	8.5	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	9	μA
I_{RRM}		$T_j=125^\circ\text{C}$	5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	0.7	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (DC)	45	$^\circ\text{C/W}$

ORDERING INFORMATION



MARKING

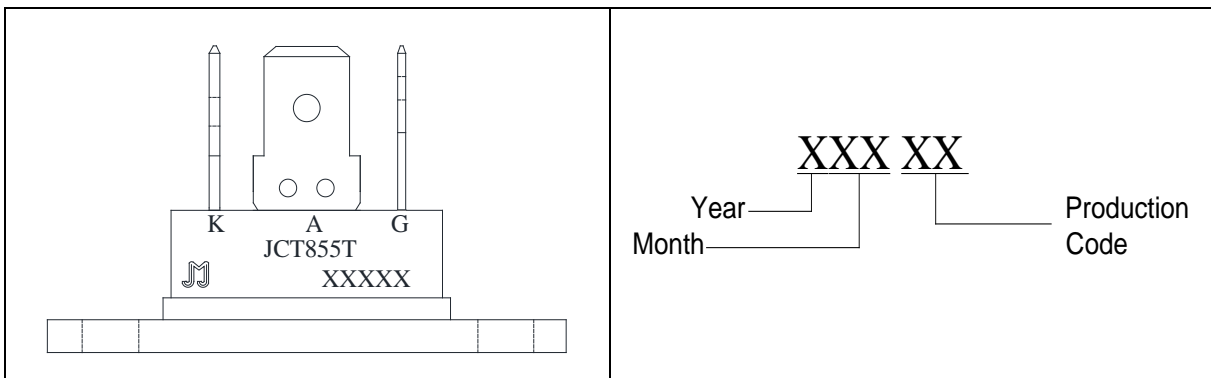


FIG.1 Maximum power dissipation versus RMS on-state current

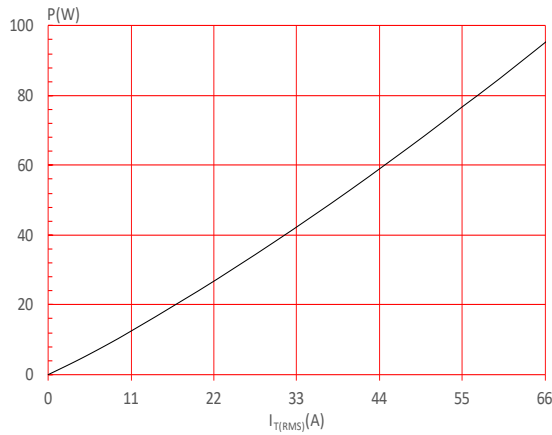


FIG.2: RMS on-state current versus case temperature

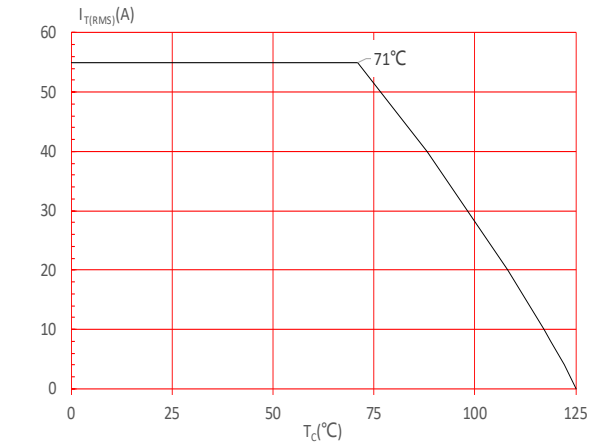


FIG.3: Surge peak on-state current versus number of cycles

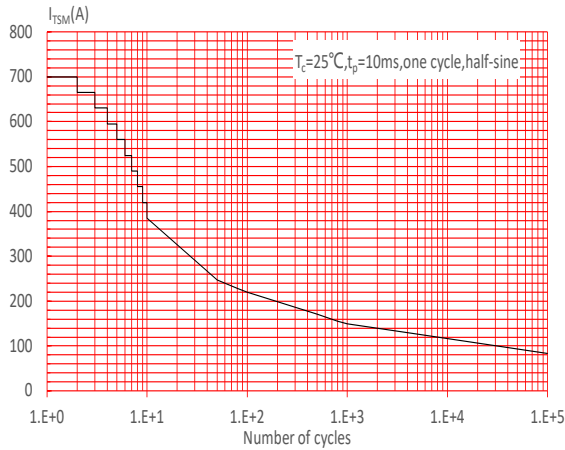


FIG.4: On-state characteristics

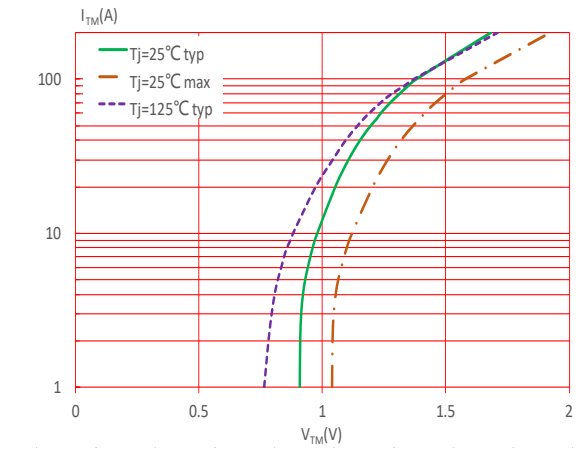


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 200\text{A}/\mu\text{s}$)

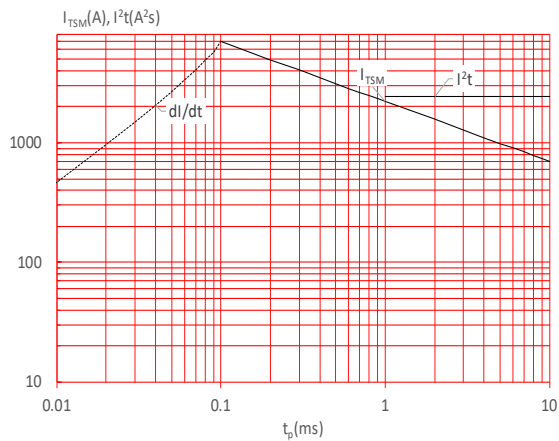


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

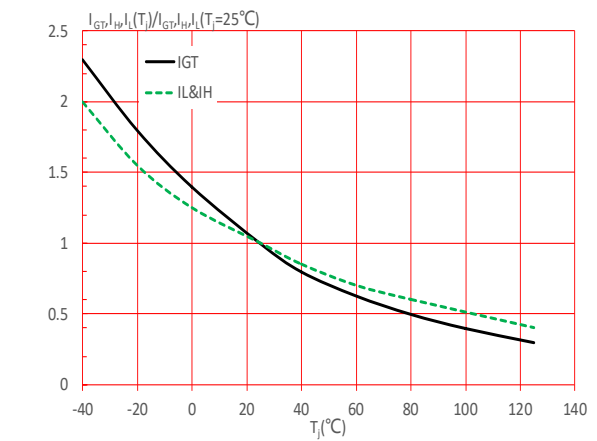
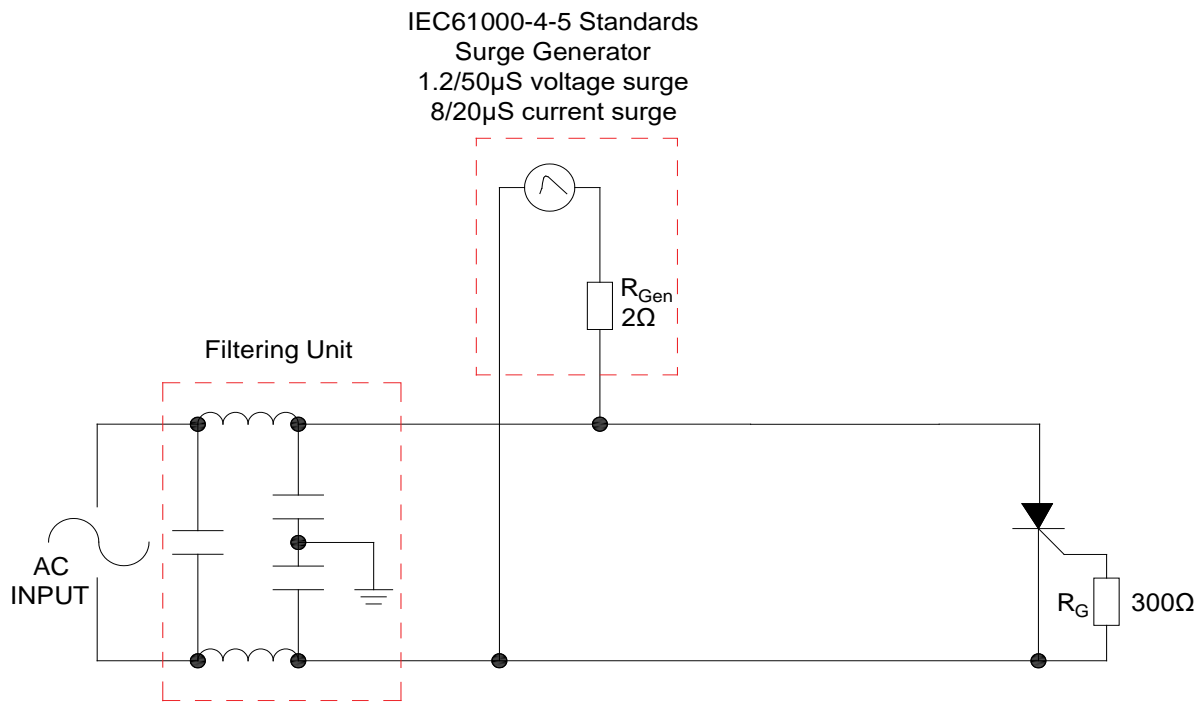


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



SHAPING AND SOLDERING PARAMETERS

Refer to «Instructions for installation of plastic-sealed in-line power devices» released by JieJie

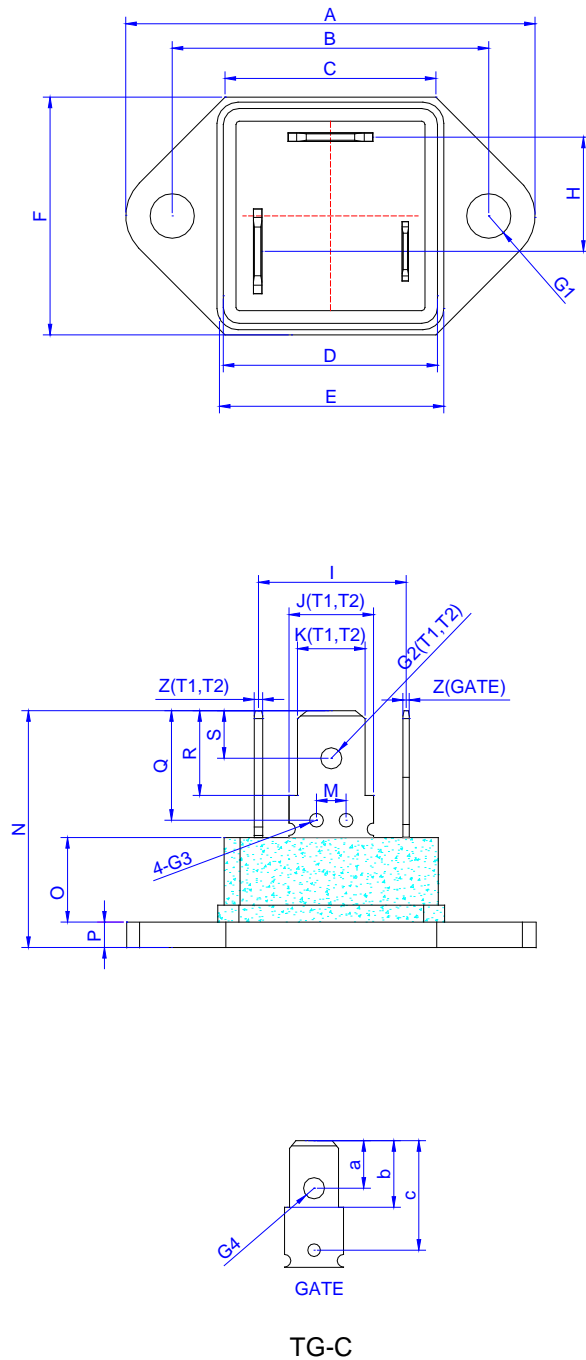
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT855T	800	10-50	TG-C	10	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			39.2			1.543
B	29.8	30.0	30.2	1.173	1.181	1.189
C			20.2			0.795
D			20.5			0.807
E			21.6			0.85
F			23			0.905
G1	Φ4.1	Φ4.2	Φ4.3	Φ0.161	Φ0.165	Φ0.169
H		10.3			0.406	
I		13.9			0.547	
J(T1,T2)		8			0.315	
K(T1,T2)		6.4			0.252	
M	2.7	3.0	3.3	0.106	0.118	0.130
N			22.8			0.898
O		8.2			0.323	
P		2.5			0.098	
Q	9.45	9.75	10.1	0.374	0.383	0.398
R	7.8	7.95	8.1	0.307	0.313	0.319
S	4.3	4.5	4.7	0.169	0.177	0.185
Z(T1,T2)	0.78	0.8	0.85	0.0307	0.0315	0.0335
G2(T1,T2)		Φ2	Φ2.2		Φ0.079	Φ0.087
G3	Φ1.1	Φ1.3	Φ1.5	Φ0.043	Φ0.051	Φ0.059
G4		Φ1.55	Φ1.75		Φ0.061	Φ0.069
a	2.95	3.15	3.35	0.116	0.124	0.132
b	6.2	6.35	6.5	0.244	0.25	0.256
c	9.35	9.75	10	0.368	0.384	0.393
Z(GATE)	0.58	0.6	0.65	0.0228	0.0236	0.0256
J(GATE)		5.6			0.221	
K(GATE)		4.65			0.183	

DELIVERY MODE

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TG-C	TUBE	10	100	500

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